

PUBLICATION NUMBER : 07045542
 PUBLICATION DATE : 14-02-95

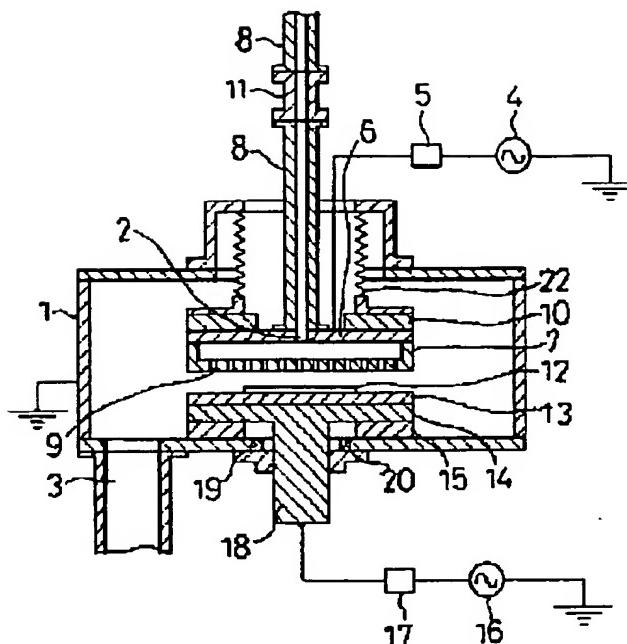
APPLICATION DATE : 03-08-93
 APPLICATION NUMBER : 05192215

APPLICANT : MATSUSHITA ELECTRIC IND CO LTD;

INVENTOR : HOUCHIN RIYUUZOU;

INT.CL. : H01L 21/205 H01L 21/3205 // H01L 21/31

TITLE : PLASMA CVD DEVICE AND METHOD



ABSTRACT : PURPOSE: To enable the flat film in high stepped part covering coefficient to be deposition-formed by a method wherein the title plasma CVD device is provided with a means for feeding a substrate mounting base with a specific low-frequency power, another means for feeding a plasma discharging electrode oppositely oriented in the substrate mounting base with a high-frequency power and a bellows freely lifting the plasma discharging electrode.

CONSTITUTION: The title plasma CVD device is provided with a low-frequency oscillator 16 feeding a substrate mounting base 13 with low-frequency power of 200KHz-1MHz, a high-frequency oscillator 4 feeding a plasma discharging electrode 7 oppositely arranged on the substrate mounting base 13 with high-frequency power as well as an elastic cylindrical bellows 22 supporting the plasma discharging electrode 7 in free-lifting mode and adjusting the interval between the substrate mounting base 13 and the plasma discharging electrode 7. Furthermore, said interval and the pressure in a reaction chamber are adjusted so that the stage of feeding both high and low frequency powers and the stage of feeding the low-frequency power only may be combined with each other to deposit flat films on a substrate.

COPYRIGHT: (C)1995,JPO